

Form PTO-1449

U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket No.
5649-482Serial No.
09/441,753

10/763,588

LIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)Applicants:
Gehrke et al.Filing Date:
November 17, 1999GAU:
2812

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Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
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Maria Guevara

Date Considered:

1-27-05

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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Gehrke et al.			
				Filing Date: November 17, 1999			
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